

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

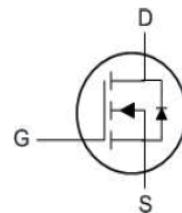
Product Summary**RoHS**

BVDSS	RDSON	ID
60V	6mΩ	80A

Description

The 80N06 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 80N06 meet the RoHS and Green Product, requirement 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source voltage	60	V
V _{GS}	Gate-Source voltage	±25	V
I _D	Continuous Drain Current	80	A
		52	
I _{DM}	Pulsed Drain Current ^{note1}	320	A
EAS	Single Pulse Avalanche Energy ^{note2}	169	mJ
P _D	Total Power Dissipation	108	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
R _{θJC}	Thermal Resistance,Junction-to-Case	1.4	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$,	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=10\text{V}$, $I_D=30\text{A}$	-	5.3	7	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	4136	-	pF
C_{oss}	Output Capacitance		-	286	-	pF
C_{rss}	Reverse Transfer Capacitance		-	257	-	pF
Q_g	Total Gate Charge	$V_{DS}=30\text{V}$, $I_D=30\text{A}$, $V_{GS}=10\text{V}$	-	90	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	18	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30\text{V}$, $I_D=30\text{A}$, $R_G=1.8\Omega$, $V_{GS}=10\text{V}$	-	9	-	ns
t_r	Turn-on Rise Time		-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	40	-	ns
t_f	Turn-off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	80	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	320	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_S=30\text{A}$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=30\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$	-	33	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge	-	46	-	-	nC

Note :

- 1.Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
- 2.EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=26\text{A}$
- 3.Pulse Test: Pulse Width $\leqslant 300\mu\text{s}$, Duty Cycle $\leqslant 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

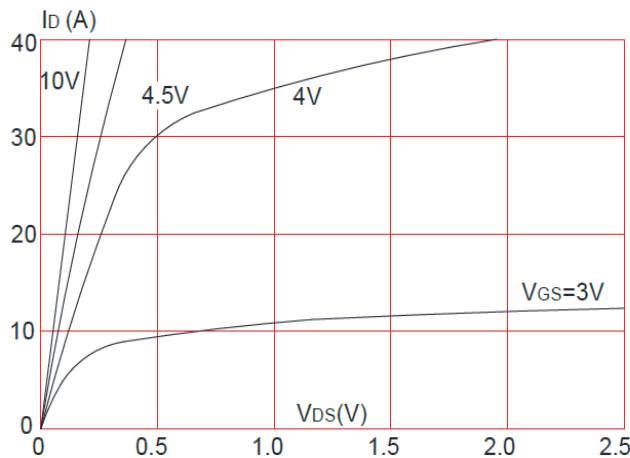


Figure 2: Typical Transfer Characteristics

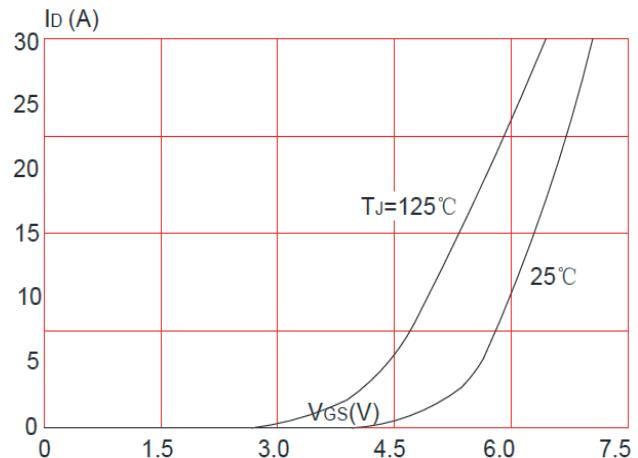


Figure 3: On-resistance vs. Drain Current

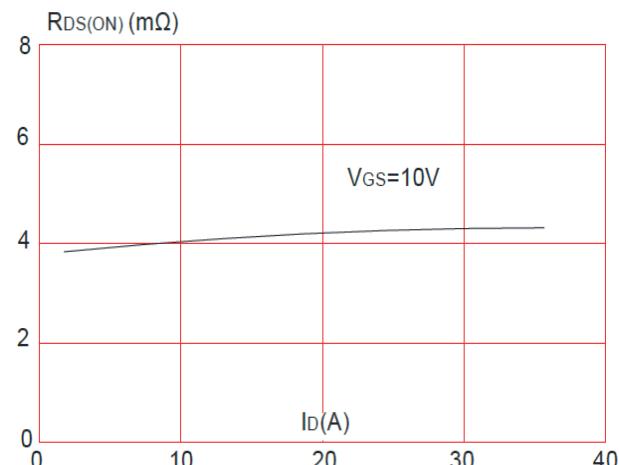


Figure 4: Body Diode Characteristics

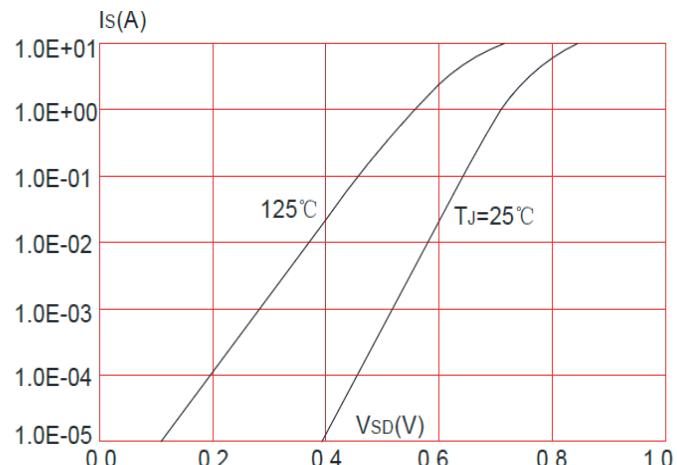


Figure 5: Gate Charge Characteristics

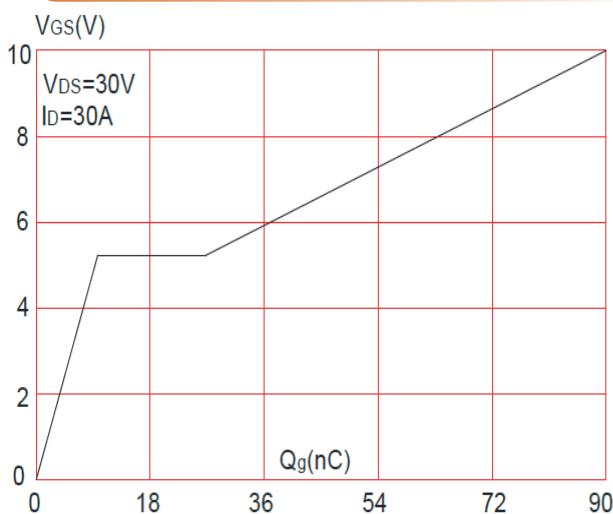
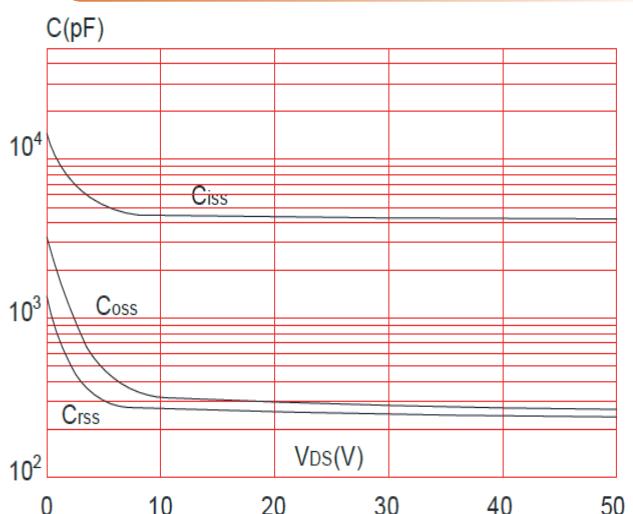


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage

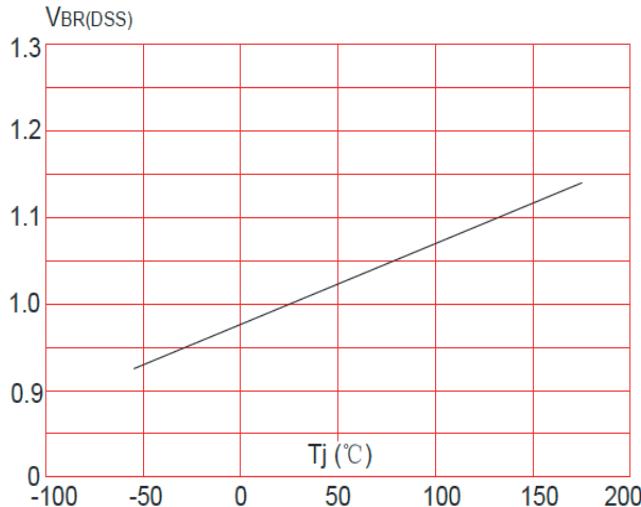


Figure 8: Normalized on Resistance vs. J_f

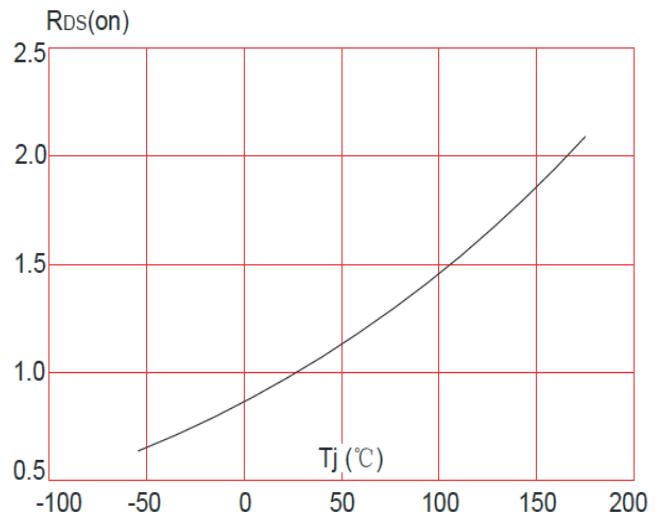


Figure 9: Maximum Safe Operating Area

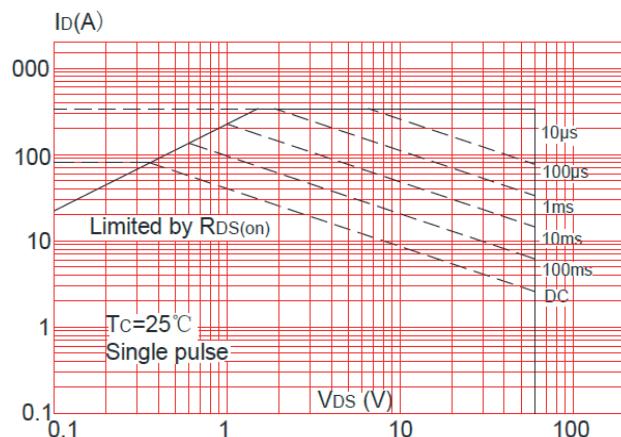


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

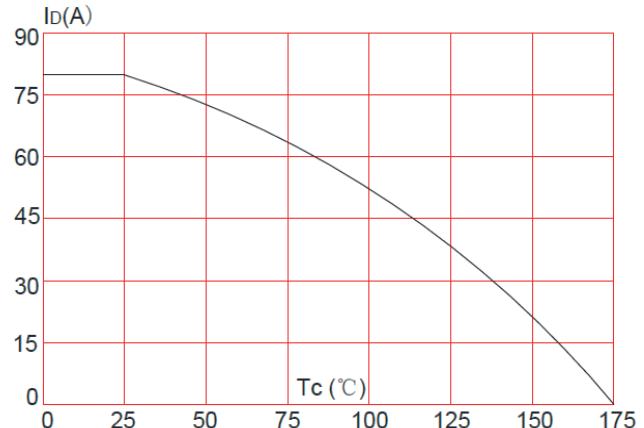
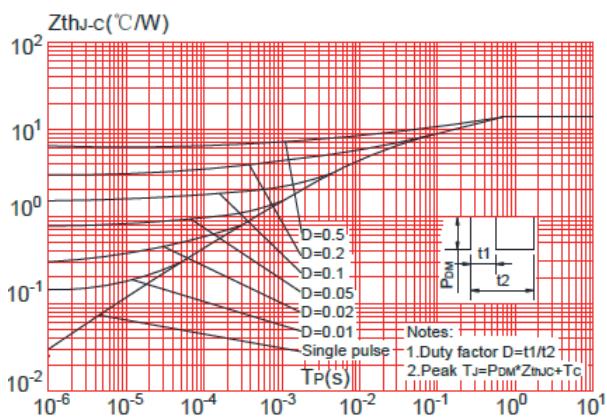
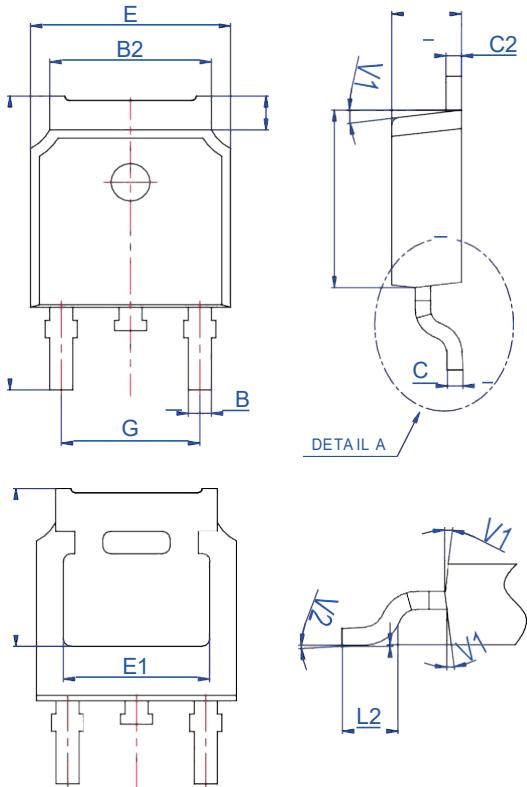


Figure 11: Maximum Effective Transient Thermal Resistance



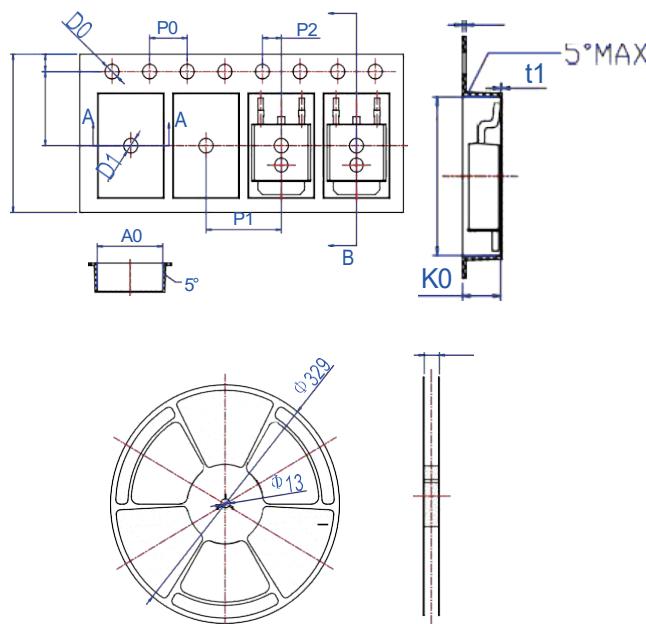


Package Mechanical Data-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.1		2.5	0.083		0.098
A2	0		0.1	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.4		0.6	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.9		6.3	0.232		0.248
D1	5.30REF			0.209REF		
E	6.4		6.8	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.5		10.7	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1	7°			7°		
V2	0°			6°		

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.9	16	16.1	0.626	0.63	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.4	7.5	7.6	0.291	0.295	0.299
D0	1.4	1.5	1.6	0.055	0.059	0.063
D1	1.4	1.5	1.6	0.055	0.059	0.063
P0	3.9	4	4.1	0.154	0.157	0.161
P1	7.9	8	8.1	0.311	0.315	0.319
P2	1.9	2	2.1	0.075	0.079	0.083
A0	6.85	6.9	7	0.27	0.271	0.276
B0	10.45	10.5	10.6	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.1			0.004		
10P0	39.8	40	40.2	1.567	1.575	1.583